

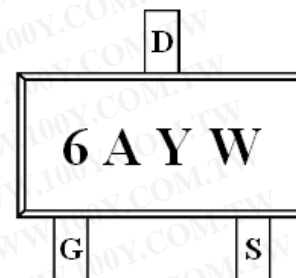
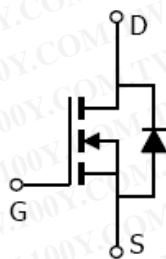
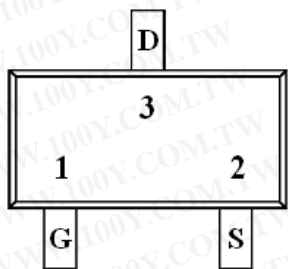


General Description

AFN2306A, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Pin Description (SOT-23)



Application

- Portable Equipment
- Battery Powered System
- Net Working System

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN2306AS23RG	6AYW	SOT-23	Tape & Reel	3000 EA

- ※ 6A parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFN2306AS23RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

($T_A=25^\circ\text{C}$ Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V_{DSS}	20	V
Gate –Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current($T_J=150^\circ\text{C}$)	I_D	$T_A=25^\circ\text{C}$	1.8
		$T_A=70^\circ\text{C}$	1.2
Pulsed Drain Current	I_{DM}	6	A
Continuous Source Current(Diode Conduction)	I_S	1	A
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	1.25
		$T_A=70^\circ\text{C}$	0.8
Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55/150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ\text{C/W}$

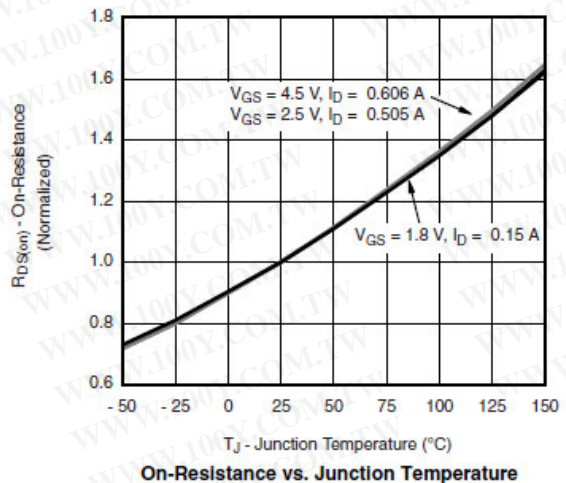
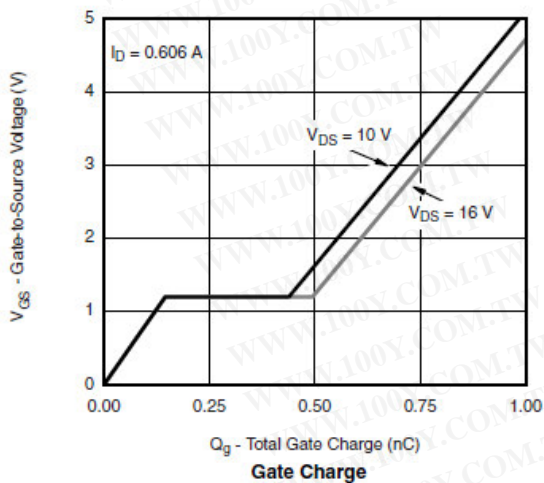
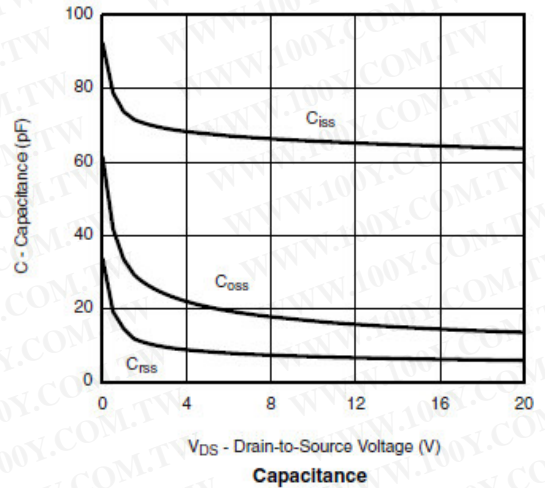
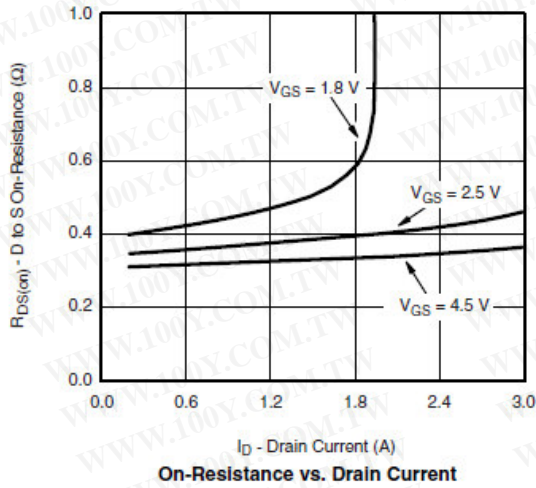
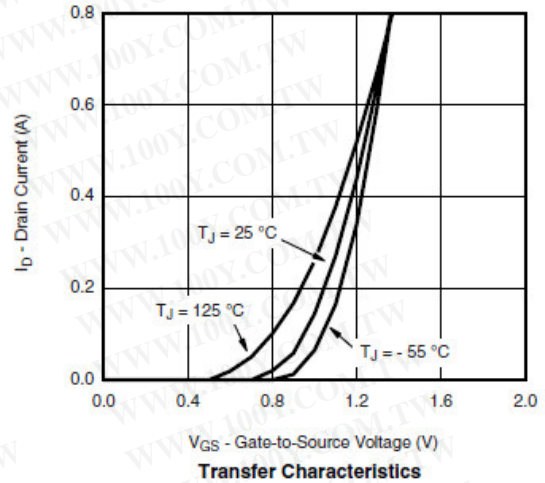
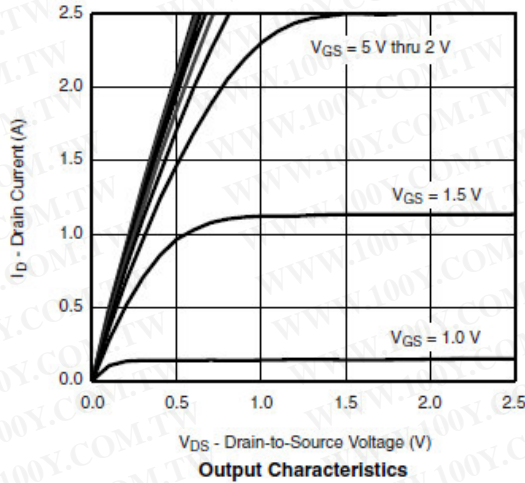
Electrical Characteristics

($T_A=25^\circ\text{C}$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu\text{A}$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.4		1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	uA
		$V_{DS}=20V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	1.8			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=1.8A$		220	280	m Ω
		$V_{GS}=2.5V, I_D=1.5A$		260	340	
		$V_{GS}=1.8V, I_D=1.2A$		540	750	
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=1.0A$		1		S
Diode Forward Voltage	V_{SD}	$I_S=1.0A, V_{GS}=0V$		0.65	1.2	V
Dynamic						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V$ $f=1\text{MHz}$		70		pF
Output Capacitance	C_{oss}			20		
Reverse Transfer Capacitance	C_{rss}			8		
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V$ $I_D \equiv 1.2A$		1.06	1.38	nC
Gate-Source Charge	Q_{gs}			0.18		
Gate-Drain Charge	Q_{gd}			0.32		
Turn-On Time	$t_{d(on)}$	$V_{DD}=10V, R_L=20\Omega$ $I_D \equiv 1.2A, V_{GEN}=4.5V$ $R_G=1\Omega$		18	26	ns
	t_r			20	28	
Turn-Off Time	$t_{d(off)}$			70	110	
	t_f			25	40	

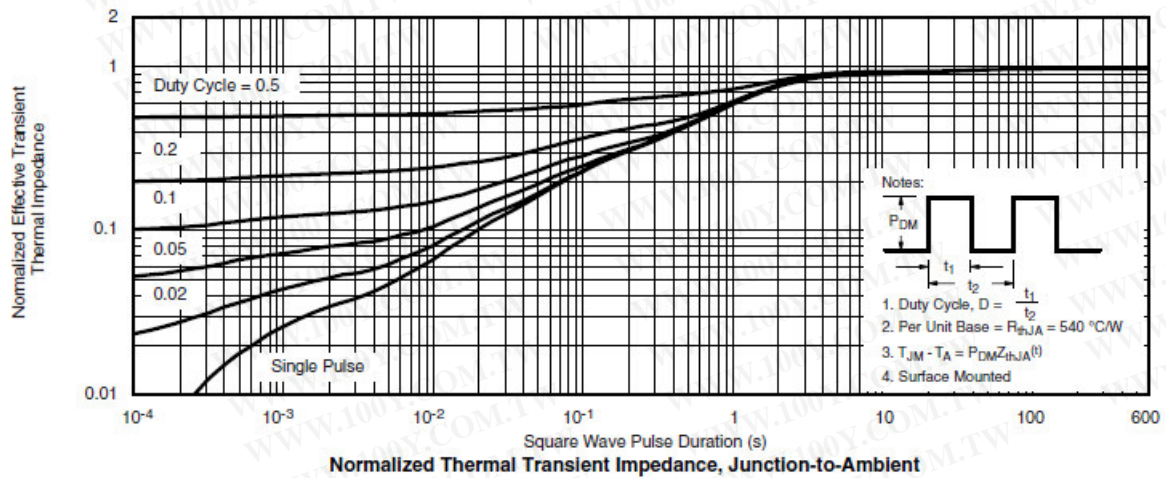
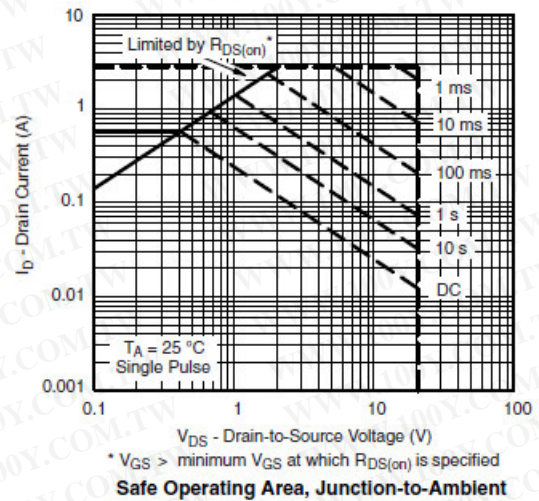
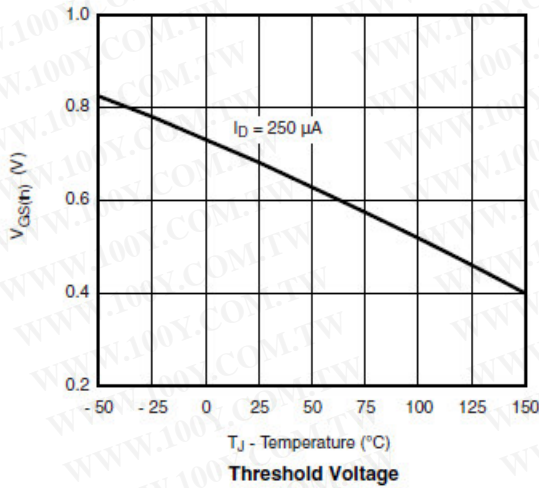
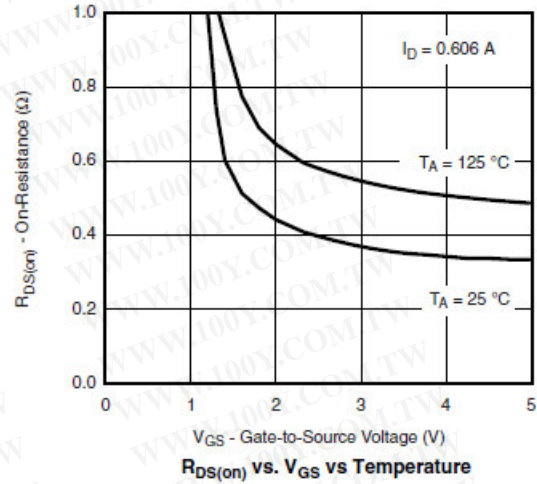
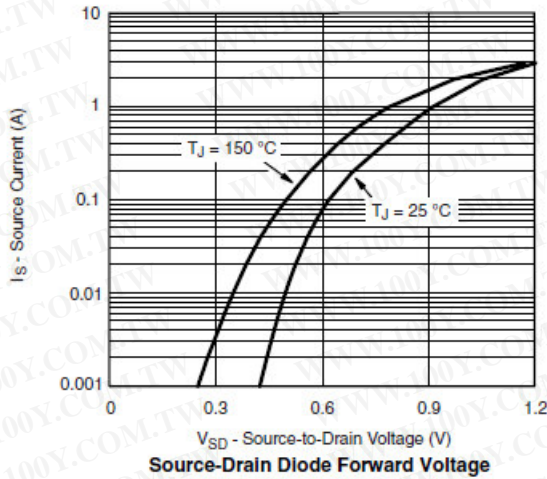


Typical Characteristics





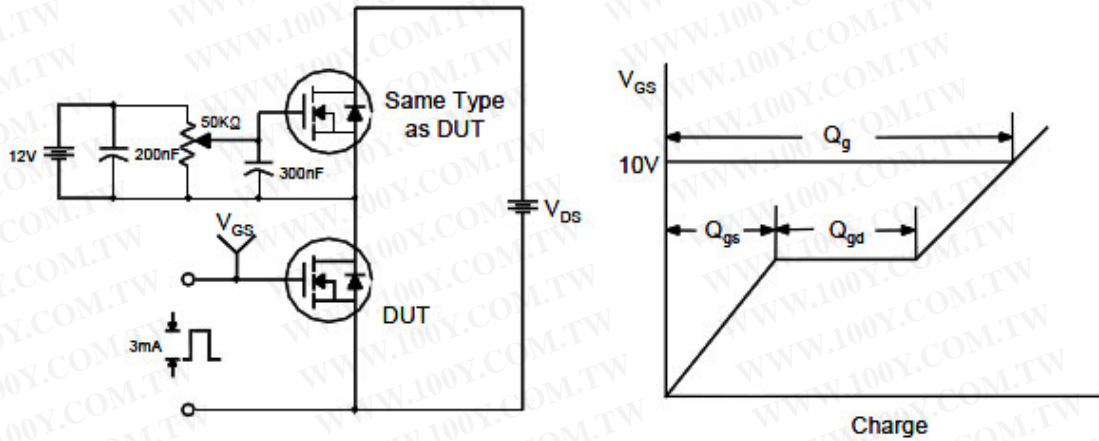
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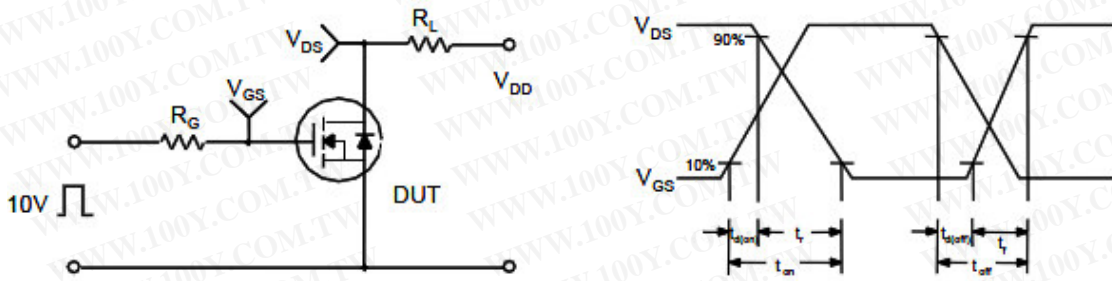


Typical Characteristics

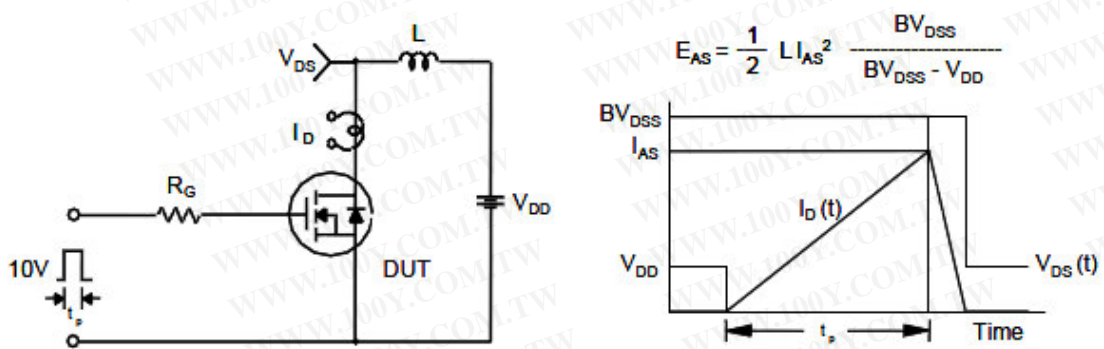
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

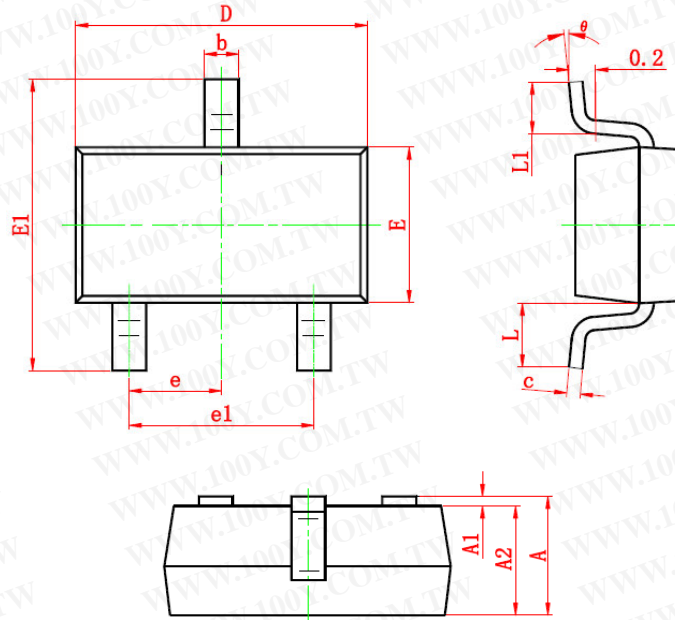


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°